Lecture 18: Memory Hierarchy— Main Memory and Enhancing its Performance

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Review: Reducing Miss Penalty Summary

- Five techniques
 - Read priority over write on miss
 - Subblock placement
 - Early Restart and Critical Word First on miss
 - Non-blocking Caches (Hit Under Miss)
 - Second Level Cache

• Can be applied recursively to Multilevel Caches

 Danger is that time to DRAM will grow with multiple levels in between

Review: Improving Cache Performance

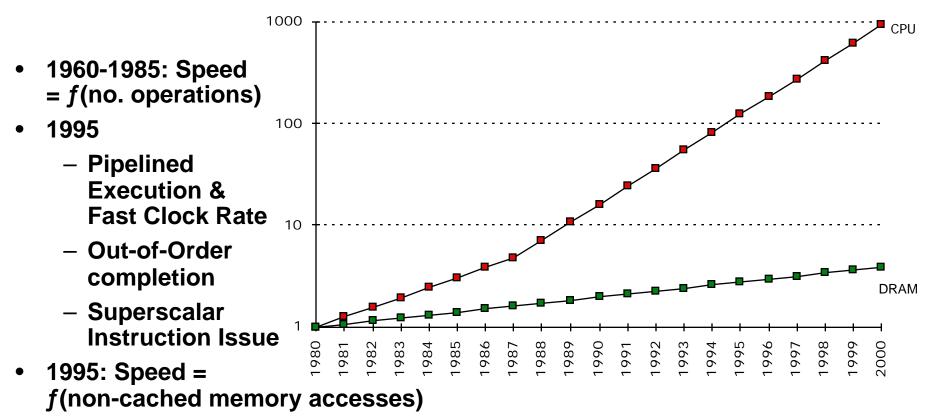
- 1. Reduce the miss rate,
- 2. Reduce the miss penalty, or
- 3. Reduce the time to hit in the cache

Fast hit times by small and simple caches Fast hits via avoiding virtual address translation Fast hits via pipelined writes Fast writes on misses via small subblocks

Review: Cache Optimization Summary

Technique	MR	MP	HT	Complexity
Larger Block Size	+	_		0
Higher Associativity	+		-	1
Victim Caches	+			2
Pseudo-Associative Caches	+			2
HW Prefetching of Instr/Data	+			2
Compiler Controlled Prefetching	+			3
Compiler Reduce Misses	+			0
Priority to Read Misses		+		1
Subblock Placement		+	+	1
Early Restart & Critical Word 1st		+		2
Non-Blocking Caches		+		3
Second Level Caches		+		2
Small & Simple Caches	_		+	0
Avoiding Address Translation			+	2
Pipelining Writes			+	1

Review: What is the Impact of What You've Learned About Caches?



- What does this mean to
 - Compilers?, Operating Systems?, Algorithms? Data Structures?

Main Memory Background

• Performance of Main Memory:

- Latency: Cache Miss Penalty
 - » Access Time: time between request and word arrives
 - » Cycle Time: time between requests
- Bandwidth: I/O & Large Block Miss Penalty (L2)

Main Memory is *DRAM*: Dynamic Random Access Memory

- Dynamic since needs to be refreshed periodically (8 ms)
- Addresses divided into 2 halves (Memory as a 2D matrix):
 - » RAS or Row Access Strobe
 - » CAS or Column Access Strobe

• Cache uses **SRAM**: Static Random Access Memory

- No refresh (6 transistors/bit vs. 1 transistor/bit)
- Address not divided

Size: DRAM/SRAM 4-8, Cost/Cycle time: SRAM/DRAM 8-16

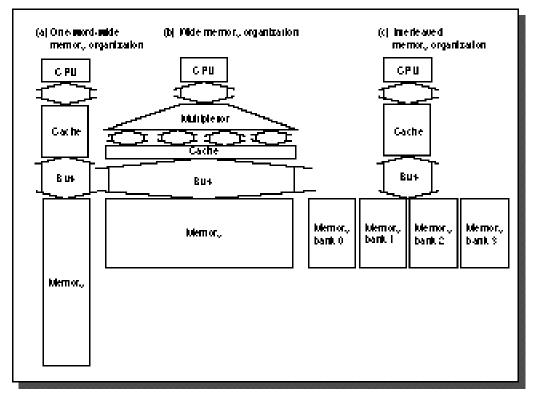
Main Memory Performance

• Simple:

CPU, Cache, Bus, Memory same width (32 bits)

• Wide:

- CPU/Mux 1 word; Mux/ Cache, Bus, Memory N words (Alpha: 64 bits & 256 bits)
- Interleaved:
 - CPU, Cache, Bus 1 word: Memory N Modules (4 Modules); example is word interleaved



Main Memory Performance

- Timing model
 - 1 to send address,
 - 6 access time, 1 to send data
 - Cache Block is 4 words
- **Simple M.P.** = 4 x (1+6+1) = 32
- Wide M.P. = 1 + 6 + 1 = 8

Address	Bank 0	Address	Bank I	Address	Bank C	Address	Bank S
• [] [] 2 [] % [
- 4 [5] 6 [7	
8		9		10			
12		1 13		4		15	

Independent Memory Banks

- Memory banks for independent accesses vs. faster sequential accesses
 - Multiprocessor
 - I/O
 - Miss under Miss, Non-blocking Cache
- Superbank: all memory active on one block transfer
- Bank: portion within a superbank that is word interleaved

6uperbank number

Independent Memory Banks

• How many banks?

number banks number clocks to access word in bank

- For sequential accesses, otherwise will return to original bank before it has next word ready
- Increasing DRAM => fewer chips => harder to have banks

Avoiding Bank Conflicts

• Lots of banks

```
int x[256][512];
for (j = 0; j < 512; j = j+1)
for (i = 0; i < 256; i = i+1)
x[i][j] = 2 * x[i][j];</pre>
```

- Even with 128 banks, since 512 is multiple of 128, conflict
- SW: loop interchange or declaring array not power of 2
- HW: Prime number of banks
 - bank number = address mod number of banks
 - address within bank = address / number of banks
 - modulo & divide per memory access?
 - address within bank = address mod number words in bank (3, 7, 31)
 - bank number? easy if 2^N words per bank

Fast Bank Number

Chinese Remainder Theorem

As long as two sets of integers ai and bi follow these rules

 $b_i = x \mod a_i, 0$ $b_i < a_i, 0$ $x < a_0 \times a_1 \times a_2 \times ...$

and that ai and aj are co-prime if i j, then the integer x has only one solution (unambiguous mapping):

- bank number = b_0 , number of banks = a_0 (= 3 in example)
- address within bank = b_1 , number of words in bank = a_1 (= 8 in example)
- N word address 0 to N-1, prime no. banks, words power of 2

		Seq. Interleaved			Modu	eaved	
Bank Number: Addre		0	1	2	0	1	2
within Bank:	0	0	1	2	0	16	8
	1	3	4	(5)	9	1	17
	2	6	7	8	18	10	2
	3	9	10	11	3	19	11
	4	12	13	14	12	 4	20
	5	15	16	17	21	13	5
	6	18	19	20	6	22	14
	7	21	22	23	15	7	23 RHK.S96 12

Fast Memory Systems: DRAM specific

- Multiple RAS accesses: several names (page mode)
 - 64 Mbit DRAM: cycle time = 100 ns, page mode = 20 ns
- New DRAMs to address gap; what will they cost, will they survive?
 - Synchronous DRAM: Provide a clock signal to DRAM, transfer synchronous to system clock
 - **RAMBUS**: startup company; reinvent DRAM interface
 - » Each Chip a module vs. slice of memory
 - » Short bus between CPU and chips
 - » Does own refresh
 - » Variable amount of data returned
 - » 1 byte / 2 ns (500 MB/s per chip)
- Niche memory or main memory?
 - e.g., Video RAM for frame buffers, DRAM + fast serial output RHK.S96 13

Main Memory Summary

- Wider Memory
- Interleaved Memory: for sequential or independent accesses
- Avoiding bank conflicts: SW & HW
- DRAM specific optimizations: page mode & Specialty DRAM